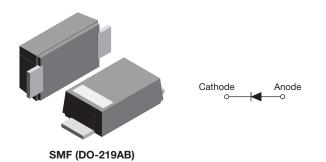
RoHS

COMPLIANT HALOGEN

FREE

**Vishay Semiconductors** 

## Hyperfast Rectifier, 1 A FRED Pt<sup>®</sup>



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PRODUCT SUMMARY				
Package	DO-219AB (SMF)			
I <sub>F(AV)</sub>	1 A			
V <sub>R</sub>	100 V			
V <sub>F</sub> at I <sub>F</sub>	0.93 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			

### FEATURES

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V <sub>RRM</sub>		100	V
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	^
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	40	A
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to 175	°C

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	100	-	-	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 A	-	0.87	0.93	V
Torward voltage		I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C	-	0.74	0.8	
Reverse leakage current	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	2	
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μA
Junction capacitance	CT	V <sub>R</sub> = 100 V	-	5	-	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F$ = 1.0 A, $dI_F/dt$ = 50 A/µs, $V_R$ = 30 V		-	26	-	
	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	ns
		T <sub>J</sub> = 125 °C		-	23	-	
Deals recovery ourrent		T <sub>J</sub> = 25 °C	$I_F = 1 A$	-	1.6	-	А
Peak recovery current I <sub>RRM</sub>	IRRM	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 160 V	-	2.5	-	A
Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	13	-	nC	
	T <sub>J</sub> = 125 °C		-	30	-	no	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case	R <sub>thJC</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	-0/w
Approvimete weight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		А	H	•

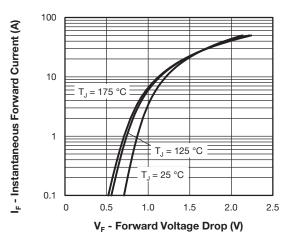
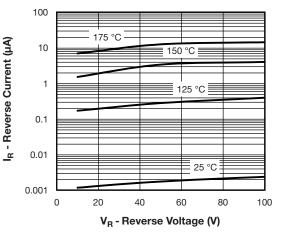
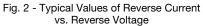


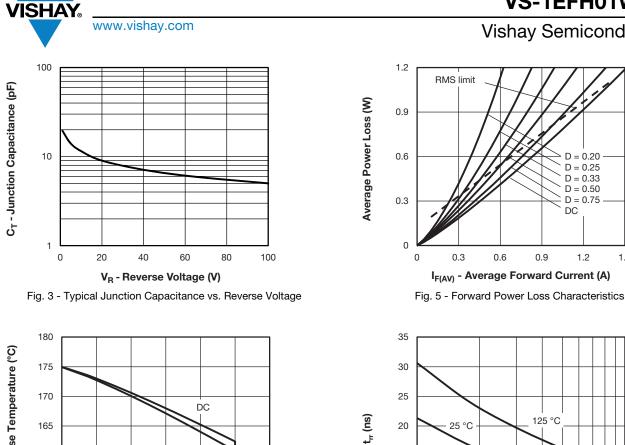
Fig. 1 - Typical Forward Voltage Drop Characteristics





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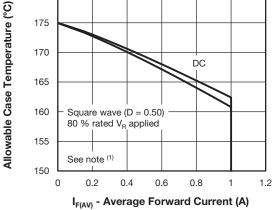
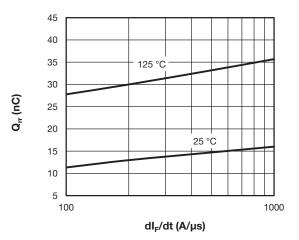


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



15

10

5

100

Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = Forward Power Loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see Fig. 6);  $Pd_{REV}$  = Inverse Power Loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

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VS-1EFH01W-M3

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D = 0.20D = 0.25 D = 0.33D = 0.50

D = 0.75 DC

1.2

1.5

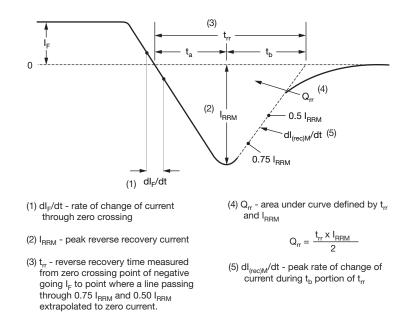
1000

dl<sub>F</sub>/dt (A/µs)

Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt



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Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION (Example)						
PREFERRED P/N	PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-1EFH01W-M3-18	10 000	10 000	13"diameter plastic tape and reel			

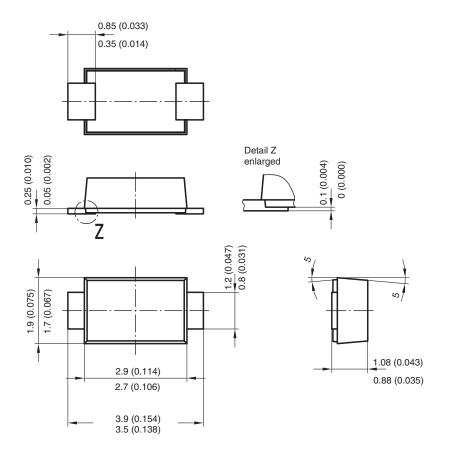
LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95563			
Packaging information	www.vishay.com/doc?95577			



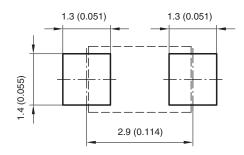
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# DO-219AB (SMF)

### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



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